

Plastic-Encapsulate Diodes

Low leakage switching diode

Features

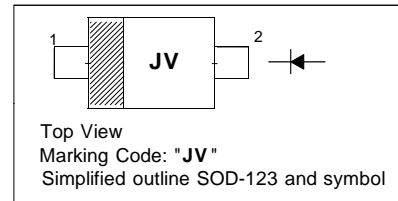
- Plastic SMD package
- Low leakage current

Application

- Low leakage current applications in surface mounted circuits.

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



MARKING: JV

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

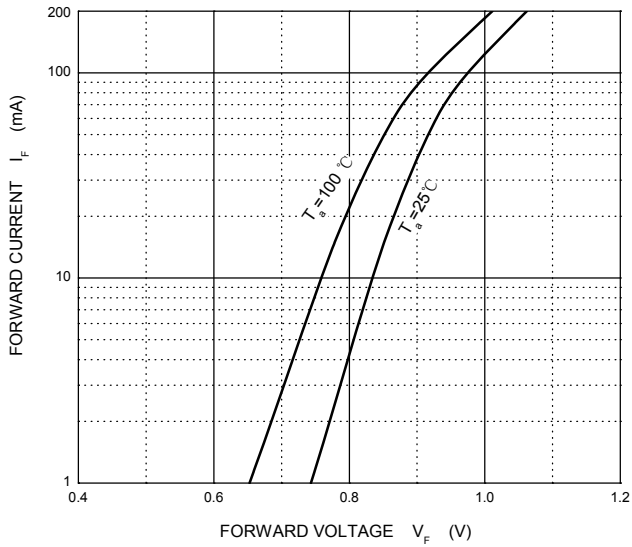
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4 1 0.5	A
		$t = 1\ \mu\text{s}$	
		$t = 1\ \text{ms}$	
		$t = 1\ \text{s}$	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

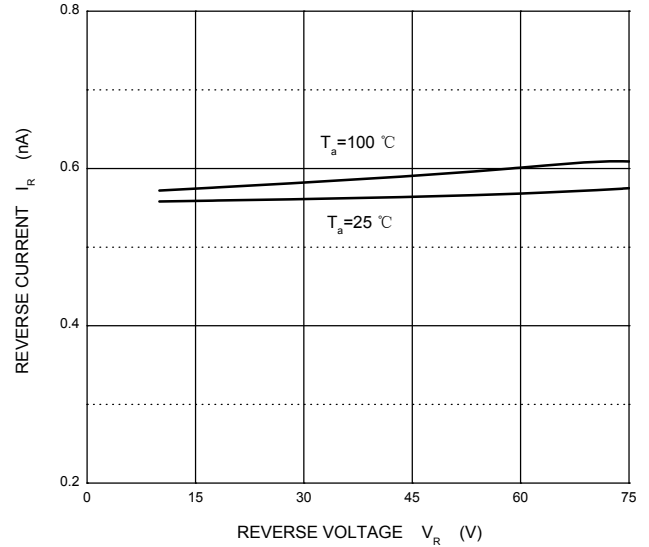
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage	V_F	-	0.9	V
at $I_F = 1\ \text{mA}$	V_F	-	1	V
at $I_F = 10\ \text{mA}$	V_F	-	1.1	V
at $I_F = 50\ \text{mA}$	V_F	-	1.25	V
at $I_F = 150\ \text{mA}$	V_F	-		
Reverse Current	I_R	-	5	nA
at $V_R = 75\ \text{V}$		-	80	
at $V_R = 75\ \text{V}, T_j = 150\text{ }^\circ\text{C}$				
Diode Capacitance	C_d	2	-	pF
at $V_R = 0, f = 1\ \text{MHz}$				
Reverse Recovery Time	t_{rr}	-	3	μs
at $I_F = I_R = 10\ \text{mA}, R_L = 100\ \Omega, i_{rr} = 0.1\ I_R$				

Typical Characteristics

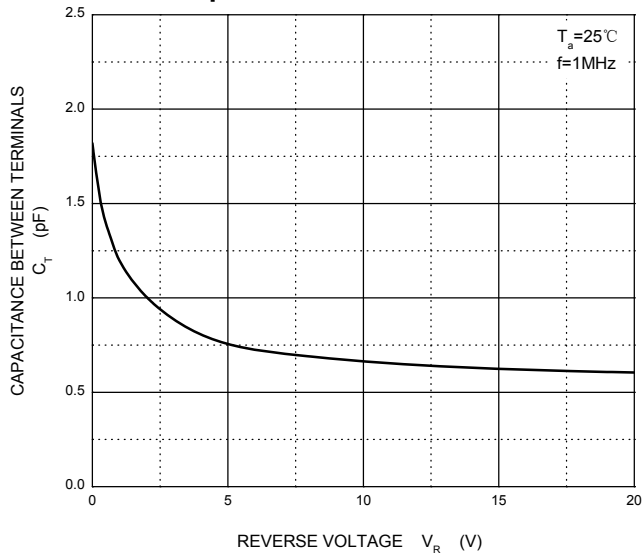
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

